TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SC5200

Power Amplifier Applications

Unit: mm

- High breakdown voltage: $V_{CEO} = 230 \text{ V (min)}$
- Complementary to 2SA1943
- Suitable for use in 100-W high fidelity audio amplifier's output stage

Maximum Ratings (Tc = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	230	V
Collector-emitter voltage	V_{CEO}	230	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	15	Α
Base current	ΙΒ	1.5	Α
Collector power dissipation (Tc = 25°C)	P _C	150	W
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55 to 150	°C

20.5MAX. 93.3±0.2 20.5MAX. 93.3

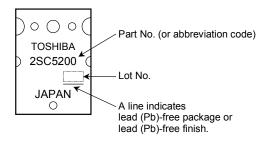
Weight: 9.75 g (typ.)

Electrical Characteristics (Tc = 25°C)

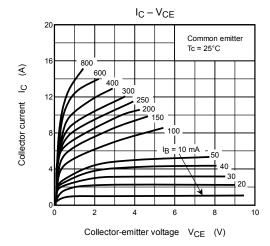
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 230 V, I _E = 0	_	_	5.0	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	5.0	μA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 50 mA, I _B = 0	230	_	_	V
DC current gain	h _{FE (1)} (Note)	V _{CE} = 5 V, I _C = 1 A	55	_	160	
	h _{FE (2)}	V _{CE} = 5 V, I _C = 7 A	35	60	_	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 8 A, I _B = 0.8 A	_	0.4	3.0	V
Base-emitter voltage	V_{BE}	V _{CE} = 5 V, I _C = 7 A	_	1.0	1.5	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 1 A	_	30	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	200	_	pF

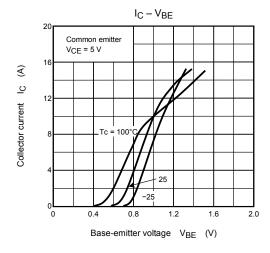
Note: hFE (1) classification R: 55 to 110, O: 80 to 160

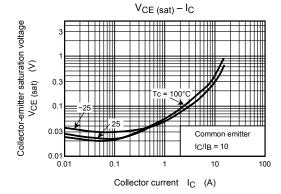
Marking

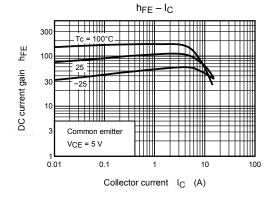


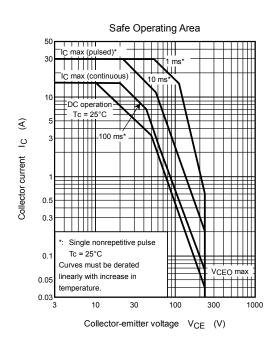
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Handbook" etc..

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